

EHB322E Digital Electronic Circuits MIDTERM I

Duration: 120 Minutes

Grading: 1) 35%, 2) 35%, 3) 30%

Exam is in closed-notes and closed-books format; calculators are allowed

For your answers please use the space provided in the exam sheet

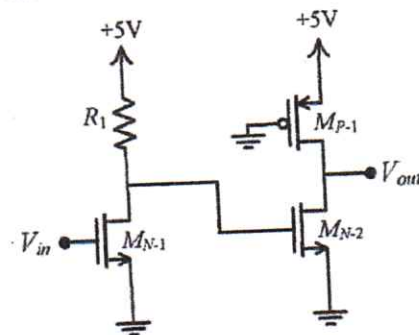
GOOD LUCK!

- 1) Consider a buffer shown below. Use the following equations for your calculations.

Saturation region current-voltage equation: $I_D = \frac{1}{2} k'_{p,n} \frac{W}{L} (V_{GS} - V_{T0,p,n})^2$

Linear region current-voltage equation: $I_D = \frac{1}{2} k'_{p,n} \frac{W}{L} [2(V_{GS} - V_{T0,p,n})V_{DS} - V_{DS}^2]$

Transistor parameters: $k_p' = \mu_p C_{ox} = 54 \mu A/V^2$, $k_n' = \mu_n C_{ox} = 96 \mu A/V^2$, $V_{TN} = 1V$, $V_{TP} = -1V$, $W_{N-1} = W_{N-2} = 12 \mu$, $L_P = L_N = 1 \mu$.



Buffer

- Find the minimum value of R_1 if $V_{in} = 5V$ results in $V_{out} = 5V$.
- Find the value of W_{P-1} if $V_{in} = 0V$ results in $V_{out} = 0.5V$.
- Find the buffer's static power consumption values when $V_{in} = 0V$ and $V_{in} = 5V$.
- Using the values found in a) and b), find the value of V_{out} if $V_{in} = 2.5V$.

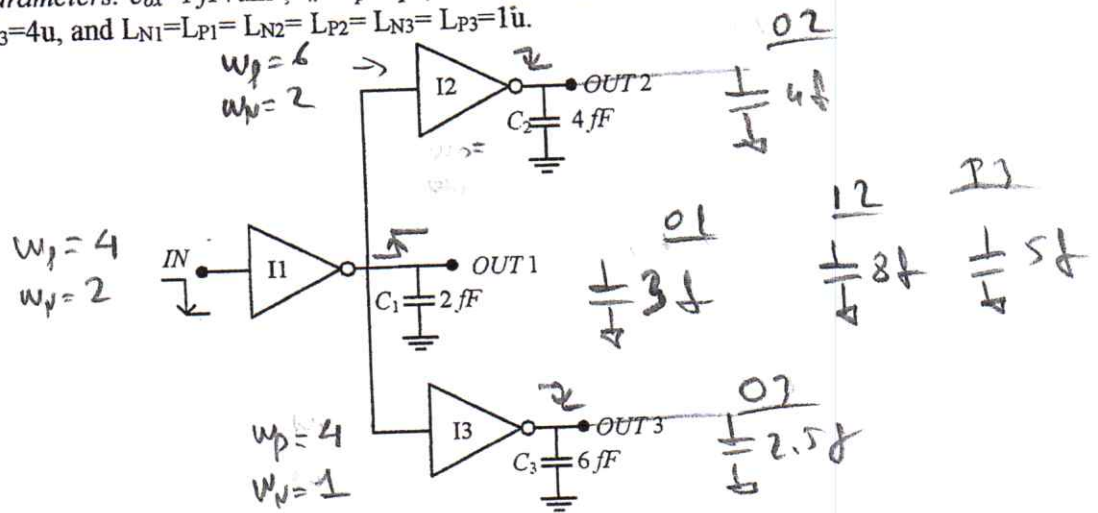
10 c) $V_{GS} = 1V \Rightarrow M_{N-1}$ is in linear region
 $I_{DN-1} = \frac{1}{2} \cdot 96 \cdot 12 \cdot [2(4) \cdot 1 - 1^2] = 4.032 \mu A$
 $\Rightarrow R_1 = (5V - 1V) / I_{DN-1} \approx 1k\Omega$

10 b) $V_{GS} = 5V \Rightarrow M_{N-1}$ is in sat. region
 $V_{out} = 0.5V$
 $\frac{1}{2} \cdot 54 \cdot W_{P-1} \cdot (4)^2 = \frac{1}{2} \cdot 96 \cdot 12 \cdot [2(4) \cdot 0.5 - 0.5^2] \Rightarrow W_{P-1} = 5 \mu$
 $I_{DP-1} = 2.16 \mu A$

5 c) $V_{in} = 0V \Rightarrow SP = 2.16 \cdot 5V \approx 10.8 mW$
 $V_{in} = 5V \Rightarrow SP = I_{DN-1} \cdot 5V \approx 20 mW$

10 d) Suppose that M_{N-1} is in sat. $\Rightarrow$ Suppose that M_{P-1} is in sat.
 $I_{DN-1} = \frac{1}{2} \cdot 96 \cdot 12 \cdot (1.5)^2 \approx 1.3 \mu A \Rightarrow V_{GSN-1} = 3.7V$
 $V_{out} = 0.82V$

- 2) Consider a circuit with three CMOS inverters and three outputs shown below. External capacitors with values of $2fF$, $4fF$, and $6fF$ are connected to output-1, output-2, and output-3, respectively. A signal switching from high to low is applied to the input. Transistor parameters: $c_{ox}=1 fF/\mu m^2$, $\tau_n=\tau_p=1ps$, $W_{N1}=2\mu$, $W_{P1}=4\mu$, $W_{N2}=2\mu$, $W_{P2}=6\mu$, $W_{N3}=1\mu$, $W_{P3}=4\mu$, and $L_{N1}=L_{P1}=L_{N2}=L_{P2}=L_{N3}=L_{P3}=1\mu$.



Digital circuit with three CMOS inverters

Propagation delays of an inverter are formulized as follows. C_L represents the total (internal and external) load capacitor of an inverter.

$$t_{PHL} = (C_L/C_N) \tau_n \quad C_N = c_{ox} W_N L_N$$

$$t_{PLH} = (C_L/C_P) \tau_p \quad C_P = c_{ox} W_P L_P$$

Suppose that $C_{GS-N} = C_N$, $C_{GS-P} = C_P$, and each inverter has an internal input capacitor of $(C_{GS-N} + C_{GS-P})$.

- Neglect the inverters' internal output capacitors and find **total propagation delay values** at output-1, output-2, and output-3.
- Suppose that each inverter has an output internal capacitor $C_{I-out} = c_{ox}(W_N + W_P)(0.5\mu m)$. Find **total propagation delay values** at output-1, output-2, and output-3.

a) for writing t_{PD} equations

$$t_{PD-1} = t_{PLH1} = \frac{C_L}{C_P} \tau_p \quad C_L = 2f + 4f + 5f = 11f$$

$$C_P = 4f$$

$$\Rightarrow t_{PD-1} = \frac{11}{4} 1ps = 2.75ps$$

$$t_{PD-2} = t_{PLH1} + t_{PHL2}$$

$$t_{PHL2} = \frac{C_L}{C_N} \tau_n \Rightarrow t_{PHL2} = 2ps$$

$$C_L = 4f \quad C_N = 2f$$

$$t_{PD-2} = 2.75ps + 2ps = 4.75ps$$

$$t_{PD-3} = t_{PLH1} + t_{PHL3}$$

$$t_{PHL3} = \frac{6}{1} ps = 6ps$$

$$t_{PD-3} = 2.75ps + 6ps = 8.75ps$$

b) for writing the equations

$$t_{PD-1} = t_{PLH1} = \frac{2 + 3 + 8 + 5}{4} ps = 4.5ps$$

$$t_{PD-2} = t_{PLH1} + t_{PHL2} = 4.5ps + \frac{8}{2} ps = 8.5ps$$

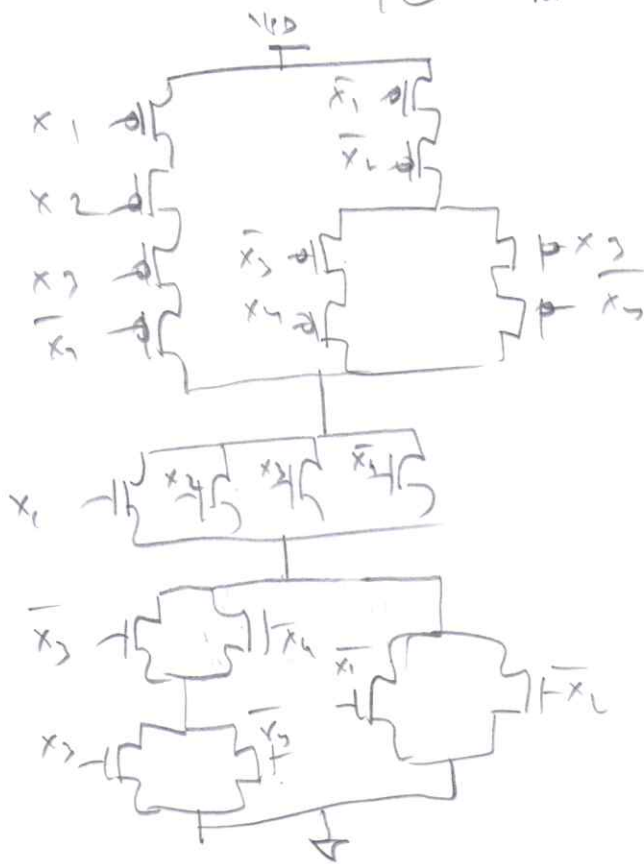
$$t_{PD-3} = t_{PLH1} + t_{PHL3} = 4.5ps + \frac{8.5}{1} ps = 13ps$$

3) Consider $f = x_1 x_2 x_3 \bar{x}_4 + x_1 x_2 \bar{x}_3 x_4 + \bar{x}_1 \bar{x}_2 \bar{x}_3 x_4$.

- a) Implement f with a **CMOS circuit** using **minimum** number of transistors. Draw the circuit. How many PMOS and NMOS transistors do you use?
- b) Suppose that both NMOS and PMOS transistors have equivalent resistance values of $1k\Omega$; a total output load capacitor is $2fF$ (Neglect all other internal capacitors). Find the **worst case (largest) t_{PHL} and t_{PLH}** values.

a) $f = x_1 x_2 (x_3 \bar{x}_4 + \bar{x}_3 x_4) + \bar{x}_1 \bar{x}_2 \bar{x}_3 x_4$ (10)

10 NMOS 10 PMOS



b) we $t_{PHL} = 0.69 (3 \times 1k\Omega) (2f) = 4.14ps$

we $t_{PLH} = 0.69 (4 \times 1k\Omega) (2f) = 5.52ps$

(10)